

CLAIMS

1. A ceramic substrate, for a semiconductor producing/examining device, having a conductor formed inside
5 thereof or on the surface thereof,

wherein said ceramic substrate has been sintered such that a fractured section thereof exhibits intergranular fracture.

2. The ceramic substrate for a semiconductor
10 producing/examining device according to claim 1,
wherein an average diameter of ceramic grains of said fractured section is 0.5 to 10 μm .

3. The ceramic substrate for a semiconductor
15 producing/examining device according to claim 1,
wherein an impurity element is locally distributed in boundaries of ceramic grains of said fractured section.

4. The ceramic substrate for a semiconductor
20 producing/examining device according to claim 1,
wherein thermal conductivity of said ceramic substrate is 100 W/m \cdot K or more.

5. The ceramic substrate for a semiconductor
25 producing/examining device according to claim 1,
wherein said ceramic substrate is constituted such that:
an impurity-existent area where an impurity element is locally distributed in triple points of crystal grains, and
an impurity element-nonexistent area where an impurity
30 is not locally distributed in the triple points of the crystal grains,
coexist therein.